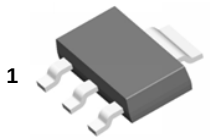
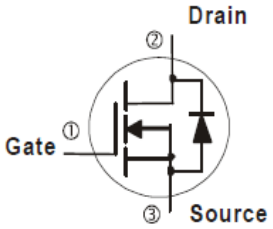
PJW3N10A

100V N-Channel Enhancement Mode MOSFET

Voltage	100 V	Current	2.2 A

SOT-223





Features

- $R_{DS(ON)}$, V_{GS}@10V,I_D@2.2A<310mΩ
- $R_{DS(ON)}$, V_{GS}@4.5V,I_D@1A<320mΩ
- Low On-Resistance
- Low input capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case : SOT-223 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.043 ounces, 0.123 grams
- Marking: W3N10A

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	2.2	A
	T_A=70°C		1.7	
Pulsed Drain Current (Note 1)		I_{DM}	4.4	A
Power Dissipation	T_A=25°C	P_D	3.1	W
	T_A=70°C		2.0	
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55~150	°C
Typical Thermal resistance - Junction to Ambient, t≦10s (Note 5)		$R_{\theta JA}$	40.3	°C/W

- Limited only By Maximum Junction Temperature

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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250uA	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	1.0	2.06	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=2.2A	-	284	310	mΩ
		V_{GS}=4.5V,I_D=1.0A	-	287	320	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V,V_{GS}=0V	-	-	1.0	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	V_{DS}=50V, I_D=2.2A, V_{GS}=10V (Note 1,2)	-	9.1	-	nC
Gate-Source Charge	Q_{gs}		-	2.1	-	
Gate-Drain Charge	Q_{gd}		-	1.4	-	
Input Capacitance	Ciss	V_{DS}=30V, V_{GS}=0V, f=1.0MHZ	-	508	-	pF
Output Capacitance	Coss		-	29	-	
Reverse Transfer Capacitance	Crss		-	18	-	
Turn-On Delay Time	$td_{(on)}$	V_{DD}=50V, I_D=2.2A, V_{GS}=10V, R_G=6Ω (Note 1,2)	-	2	-	ns
Turn-On Rise Time	t_r		-	21	-	
Turn-Off Delay Time	$td_{(off)}$		-	12	-	
Turn-Off Fall Time	t_f		-	19	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	2.2	A
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS}=0V	-	0.78	1.2	V

NOTES :

1. Pulse width≤300us, Duty cycle≤2%
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is package limited.
4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 $inch^2$ with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.

PJW3N10A

TYPICAL CHARACTERISTIC CURVES

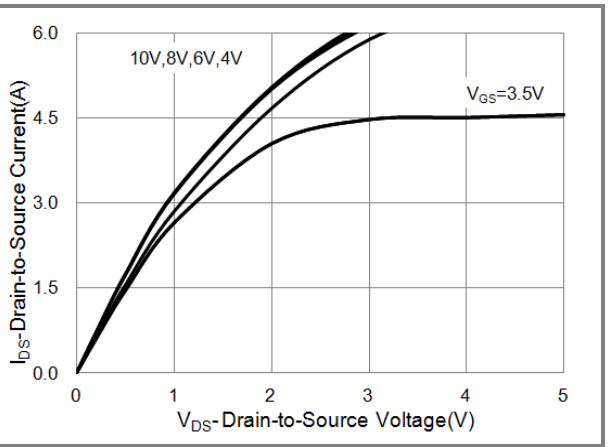

Fig.1 Output Characteristics

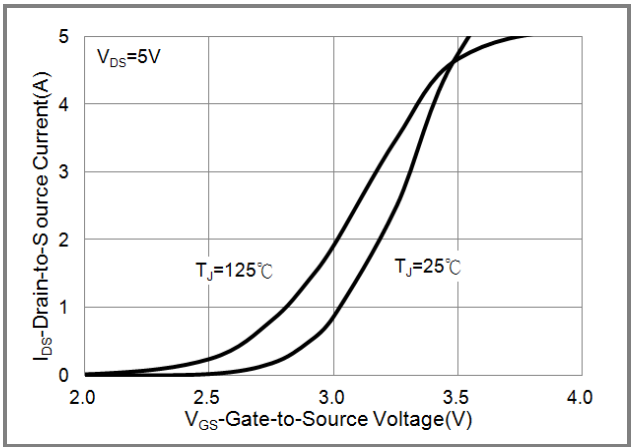

Fig.2 Transfer Characteristics

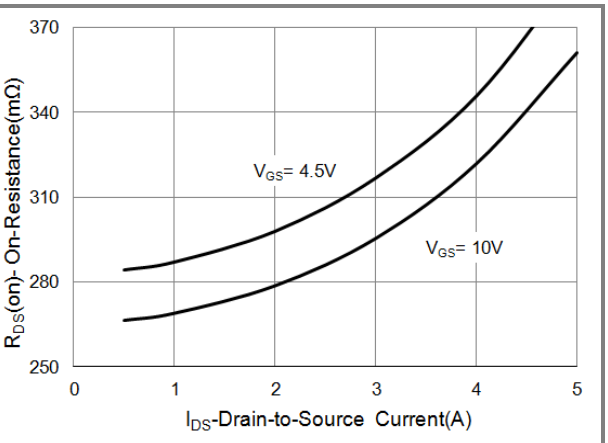

Fig.3 On-Resistance vs. Drain Current

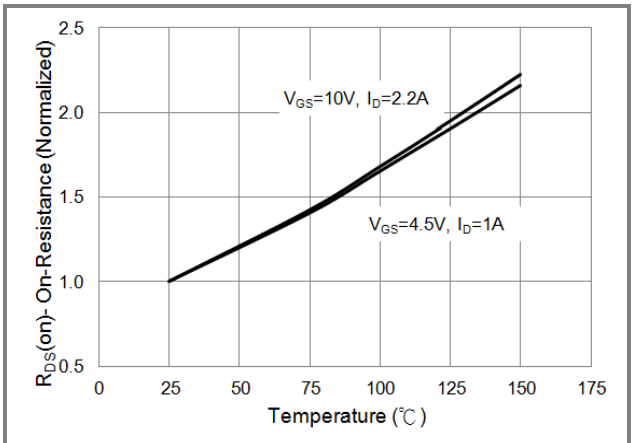

Fig.4 On-Resistance vs. Junction temperature

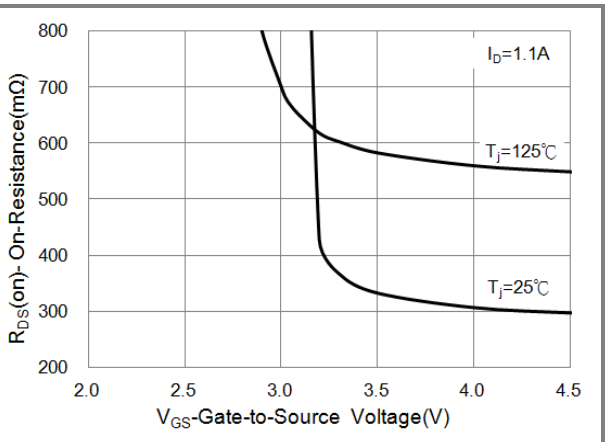

Fig.5 On-Resistance Variation with VGS.

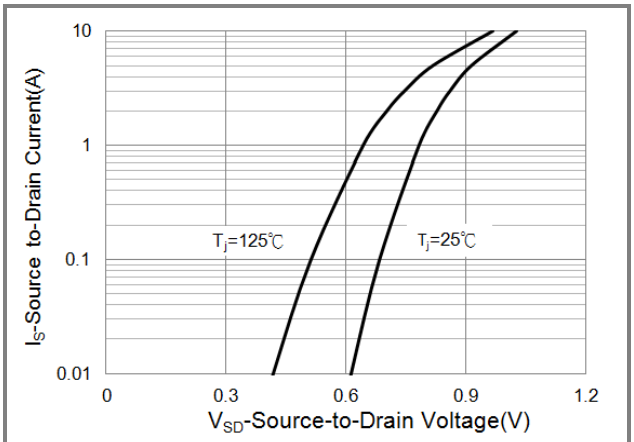

Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

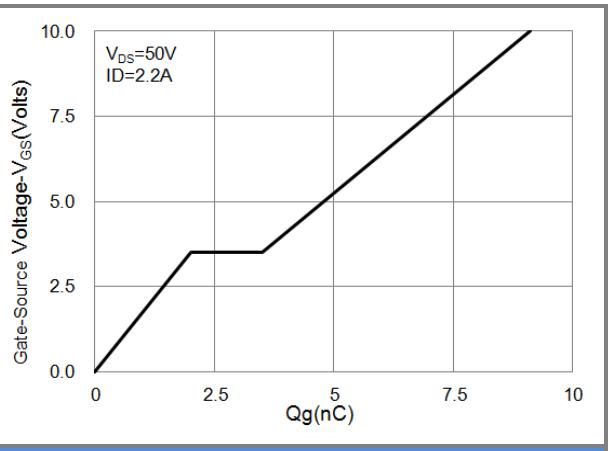

Fig.7 Gate-Charge Characteristics

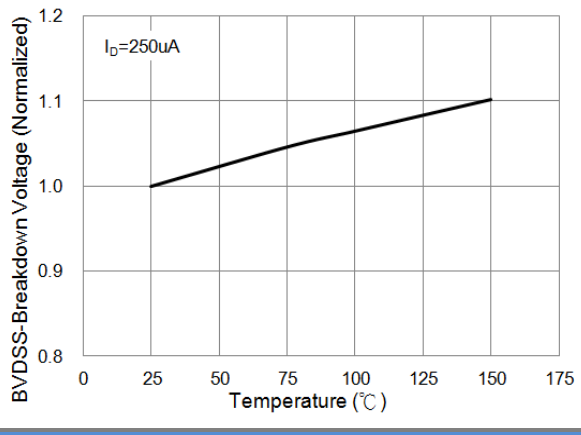

Fig.8 Breakdown Voltage Variation vs. Temperature

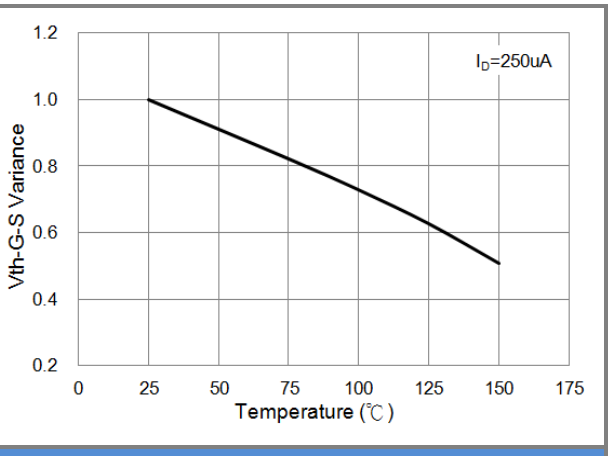

Fig.9 Threshold Voltage Variation with Temperature

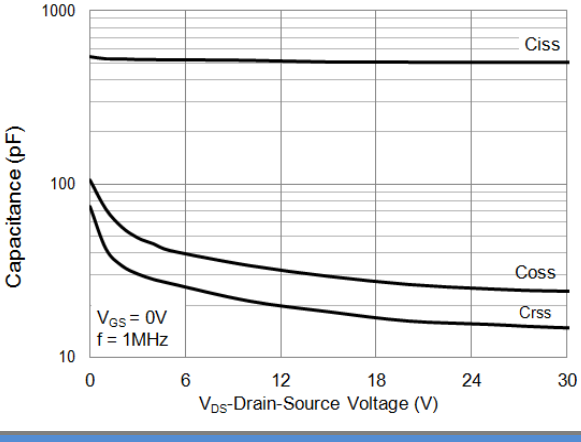

Fig.10 Capacitance vs. Drain-Source Voltage

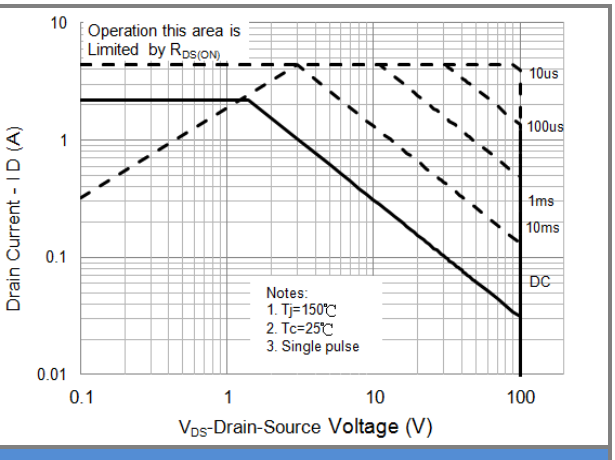

Fig.11 Maximum Safe Operating Area

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TYPICAL CHARACTERISTIC CURVES

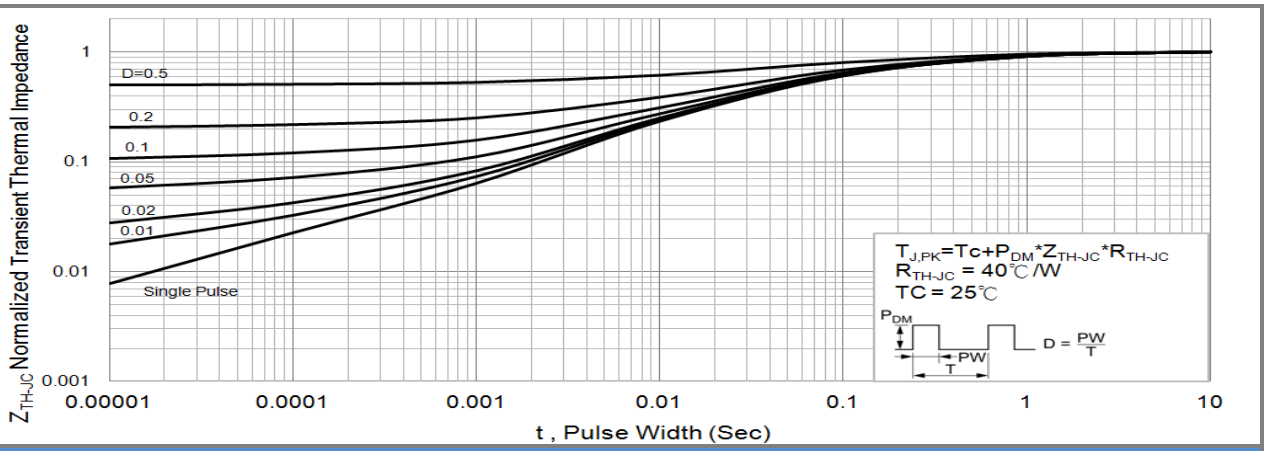

Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

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Packaging Information .

SOT-223 Dimension Unit: mm